

Amendments to the Claims:

The following listing of claims will replace all prior versions, and listings, of claims in the application:

1-14. (Canceled)

15. (Currently Amended) A semiconductor device comprising:

a semiconductor chip;

a substrate on which a an interconnecting pattern is formed; and

a binder electrically connecting the semiconductor chip and the interconnecting pattern, the binder including:

a first layer including a first resin; and

a second layer including conductive particles dispersed only in a second resin, the second layer being disposed closer to the substrate than the first layer, a coefficient of thermal expansion of the first resin being smaller than a coefficient of thermal expansion of the second resin.

16. (Original) The semiconductor device as defined in Claim 15, wherein the binder is an anisotropic conductive film.

17-18. (Canceled)

19. (Previously Presented) A circuit board on which the semiconductor device as defined in Claim 15 is mounted.

20. (Presently Presented) Electronic equipment comprising the semiconductor device as defined in Claim 15.

21-28. (Canceled)

29. (Currently Amended) The semiconductor device as defined in Claim 15, wherein a silica insulating filler is mixed only in the ~~first-layer~~ resin.

30. (Currently Amended) The semiconductor device as defined in Claim 15, wherein the second layer includes an epoxy resin.

31. (Previously Presented) The semiconductor device as defined in Claim 15, wherein conductive particles are dispersed only in the second layer.

32. (Currently Amended) The semiconductor device as defined in Claim 15,
_____ wherein the conductive particles are dispersed only in the second ~~layer~~ layer,
and
_____ wherein the second layer is thinner than the first layer, and the second ~~layer~~
resin has higher viscosity than the first ~~layer~~ resin when melted.

33. (Currently Amended) The semiconductor device as defined in Claim 15, wherein a silica insulating filler is mixed in the first ~~layer~~ resin.

34. (Currently Amended) The semiconductor device as defined in Claim 15, wherein a silica insulating filler is mixed in the first ~~layer~~ resin and the second ~~layer~~ resin, and a component ratio of the silica insulating filler in the first ~~layer~~ resin is greater than a component ratio of the silica insulating filler in the second ~~layer~~ resin.

35. (Currently Amended) The semiconductor device as defined in Claim 15, wherein at least the first resin ~~including~~ includes an epoxy resin.

36. (Previously Presented) A semiconductor device comprising:
a semiconductor chip;
a substrate on which a interconnecting pattern is formed; and
a binder electrically connecting the semiconductor chip and the
interconnecting pattern, the binder including:

a first layer including a first resin; and

a second layer including conductive particles dispersed only in a second resin, the second layer being disposed closer to the substrate than the first layer, a

modulus of elasticity of the second resin being smaller than a modulus of elasticity of the first resin.

37. (Previously Presented) The semiconductor device as defined in Claim 36, wherein the binder is an anisotropic conductive film.

38. (Currently Amended) The semiconductor device as defined in Claim 36, wherein a coefficient of thermal expansion of the first ~~layer-resin~~ is smaller than a coefficient of thermal expansion of the second ~~layer-resin~~.

39. (Previously Presented) The semiconductor device as defined in Claim 36, wherein a silica insulating filler is mixed only in the first resin.

40. (Currently Amended) The semiconductor device as defined in Claim 36, wherein a silica insulating filler is mixed in the first ~~layer-resin~~ and the second ~~layer-resin~~, and a component ratio of the silica insulating filler in the first ~~layer-resin~~ is greater than a component ratio of the silica insulating filler in the second ~~layer-resin~~.

41. (Previously Presented) The semiconductor device as defined in Claim 36, wherein the second resin includes an epoxy resin.

42. (Currently Amended) The semiconductor device as defined in Claim 36, ————— wherein conductive particles are dispersed only in the second ~~layer~~; and ————— wherein ~~layer~~, the second layer is thinner than the first layer, and the second ~~layer-resin~~ has higher viscosity than the first ~~layer-resin~~ when melted.

43. (Previously Presented) The semiconductor device as defined in Claim 36, the first resin including an epoxy resin and the second resin including a biphenyl resin.

44. (Previously Presented) A circuit board on which the semiconductor device as defined in Claim 36 is mounted.

45. (Previously Presented) Electronic equipment comprising the semiconductor device as defined in Claim 36.

46-49. (Canceled)